

**AMENDMENTS****In the Specification**

None.

**In the Claims**

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 C.F.R. §1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. §1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

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1. (Amended) A method of preparing a polishing process liquid for a semiconductor polishing process comprising:

providing a liquid;

degassifying the liquid; and

injecting a gas into the liquid to regassify the liquid, the regassification increasing a total dissolved gas concentration in the liquid to greater than or equal to 200 ppb, the regassification forming the polishing process liquid.

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SUB 2

3. (Amended) The method of Claim 1 wherein the providing provides a water comprising liquid.

4. The method of Claim 1 wherein the semiconductor polishing process comprises an etch process.

5. The method of Claim 1 wherein the semiconductor polishing process comprises a wet etch process and the liquid comprises water.

✓ ✓  
Add new Claims 39-48

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39. (New) The method of Claim 1, where degassifying the liquid comprises removing a first gas from the liquid and the gasifying the liquid comprises adding a second gas, the first gas and the second gas having different compositions.

40. (New) The method of Claim 39, where the first gas composition comprises a composition similar to that of the atmosphere and the second gas composition is an essentially non-reactive gas composition.

41. (New) The method of Claim 39, where the second gas composition comprises nitrogen and/or argon.

42. (New) The method of Claim 1, where the injected gas does not include oxygen.

43. (New) The method of Claim 1, where injecting the gas into the degassed liquid increases the total dissolved gas concentration in the liquid to from about 450 ppb to about 550 ppb.

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44. (New) The method of Claim 1, where injecting the gas into the degassed liquid increases the total dissolved gas concentration in the liquid to at least about 500 ppb.

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45. (New) The method of Claim 1, where the providing supplies a liquid having a total dissolved concentration of oxygen that is greater than or equal to 200 ppb.

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46. (New) The method of Claim 45, where the liquid provided comprises water.

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47. (New) The method of Claim 1, where injecting the gas into the degassed liquid comprises injecting the gas through a sintered filter.

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48. (New) The method of Claim 1, where the degassification and the regassification comprise a common processing step.